Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claim 1 (Currently Amended): A semiconductor device comprising:

a substrate which has a main surface;

an alignment mark which is formed on the main surface and which has a pattern, wherein the pattern in a plane view has a shape that is obtained by eliminating corners from a polygon; and

[[an]] strips of oxidation prevention cover film [[on]] that are respectively aligned above the alignment mark, that are separated from each other, and ~~formed as having~~ that are disposed in the shape of the pattern.

Claim 2 (Original): The semiconductor device as claimed in claim 1, wherein the polygon is a rectangle.

Claim 3 (Previously Presented): The semiconductor device as claimed in claim 1, wherein a width of the pattern of the alignment mark ranges from 0.6 μm to 0.8 μm.

Claim 4 (Previously Presented): The semiconductor device as claimed in claim 1, wherein the alignment mark is a metal film.

Claims 5-6 (Canceled)

Claim 7 (Currently Amended): The semiconductor device as claimed in claim 1, wherein a width of the strips ~~pattern~~ of [[the]] oxidation prevention cover film is 1 μm to several μm wider at one side than a width of the pattern of the alignment mark.

Claim 8 (Currently Amended): The semiconductor device as claimed in claim 1, wherein the strips of oxidation prevention cover film [[is]] are formed of iridium-based metal.

Claim 9 (Currently Amended): A semiconductor device comprising:

a substrate which has a main surface;

an alignment mark which is formed on the main surface and which has first through fourth ~~sub-patterns~~ mark portions,

wherein the first through fourth mark portions are arranged in a pattern so that the first and second ~~sub-patterns are arranged so as to~~ mark portions oppose each other, the third and fourth mark portions ~~sub-patterns are arranged so as to~~ oppose each other, and the first through fourth ~~sub-patterns~~ mark portions are separated from one another; and

first through fourth sections of [[an]] oxidation prevention cover film respectively ~~on the alignment mark and~~ formed as separated from each other and aligned directly above ~~as having~~ the first through fourth ~~sub-patterns~~ mark portions in the pattern.

Claim 10 (Currently Amended): The semiconductor device as claimed in claim 9, wherein a width of the first through fourth mark portions ~~sub-patterns~~ of the alignment mark ranges from 0.6 μm to 0.8 μm.

Claim 11 (Original): The semiconductor device as claimed in claim 9, wherein the alignment mark comprises a metal film.

Claims 12-13 (Canceled)

Claim 14 (Currently Amended): The semiconductor device as claimed in claim 9, wherein a width of the first through fourth ~~sub-patterns of the~~ sections of oxidation prevention cover film is 1 μm to several μm wider at one side than a width of the first through fourth mark portions ~~sub-patterns~~ of the alignment mark.

Claim 15 (Currently Amended): The semiconductor device as claimed in claim 9, wherein the oxidation prevention cover films are ~~film is~~ formed of iridium-based metal.

Claim 16 (Currently Amended): A semiconductor device comprising:

a substrate having a main surface;

an alignment mark on the main surface of the substrate, wherein the alignment mark is strip-like and has [[the]] a shape of a polygon without corners along a plane parallel to the main surface of the substrate; and

an oxidation prevention cover film aligned directly above [[on]] the alignment mark, wherein the oxidation prevention cover film is a closed-loop strip ~~strip-like~~ and has the ~~annular~~ shape of the polygon ~~along another plane parallel to the main surface of the substrate~~.

Claim 17 (Previously Presented): The semiconductor device of claim 16, wherein the polygon is a rectangle.

Claim 18 (Currently Amended): The semiconductor device of claim 17, wherein the oxidation prevention cover film has rectangular ~~annular~~ shape.

Claim 19 (Previously Presented): The semiconductor device of claim 16, wherein the alignment mark has a width ranging from 0.6 μm to 0.8 μm.

Claim 20 (Previously Presented): The semiconductor device of claim 16, wherein a width of the oxidation prevention cover film is 1 μm to several μm wider than a width of

the alignment mark.

Claim 21 (Previously Presented): The semiconductor device of claim 16, wherein the alignment mark is a metal film.

Claim 22 (Previously Presented): The semiconductor device of claim 16, wherein the oxidation prevention cover film is an iridium based metal.